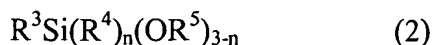
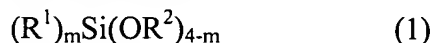


Amendments to the Claims:

1. (currently amended) A composition for forming porous film, comprising a surfactant and a solution comprising polymer obtainable by hydrolyzing and condensing, in the presence of the surfactant, one or more ~~[[of]]~~ alkoxy silanes represented by Formula (1) and one or more ~~[[of]]~~ alkoxy silanes represented by Formula (2):



wherein R^1 represents a monovalent hydrocarbon group which may be substituted or non-substituted and when there are R^1 's, the R^1 's ~~may be~~ are independently the same or different; R^2 represents an alkyl group having 1 to 4 carbons and when there are R^2 's, the R^2 's ~~may be~~ are independently the same or different; R^3 represents a straight chain or branched alkyl group having 8 to 30 carbons; R^4 represents a monovalent hydrocarbon group which may be substituted or non-substituted and when there are R^4 's, the R^4 's ~~may be~~ are independently the same or different; R^5 represents an alkyl group having 1 to 4 carbons and when there are R^5 's, the R^5 's ~~may be~~ are independently the same or different; m is an integer of 0 to 3; and n is an integer of 0 to 2.

2. (original) The composition for forming porous film according to Claim 1 wherein said surfactant is a compound which decomposes, evaporates or sublimates when heated to 400°C or less.

3. (currently amended) The composition for forming porous film according to Claim 1 ~~[[or 2]]~~ wherein said one or more of alkoxy silane represented by Formula (2) are of 0.01 to 10 parts by weight ~~toward~~ to 100 parts by weight of said one or more of the alkoxy silanes represented by Formula (1).

4. (currently amended) The composition for forming porous film according to ~~any one of Claim~~ ~~[[s]]~~ 1 ~~[[to 3]]~~ wherein said one or more of the alkoxy silanes represented by Formula (1) ~~are tetraalkoxy silane and the other compound or compounds; and an amount of the tetraalkoxy silane is 10% by weight or more~~ of tetraalkoxy silane in said alkoxy silanes represented by Formula (1).

5. (currently amended) The composition for forming porous film according to ~~any one of Claim~~[[s]] 1 [[to 4]], comprising a compound which is neutral at ordinary temperature and generates acid or alkali at 80 to 200°C.

6. (currently amended) A method for forming porous film comprising a step of applying said composition of ~~any one of Claim~~[[s]] 1 [[to 5]] on a substrate to form film and a step of transforming the film into porous film.

7. (original) The method for forming porous film according to Claim 6 wherein said step of transforming comprises a step of drying said film and a step of removing said surfactant from the dried film.

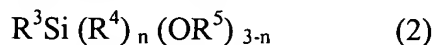
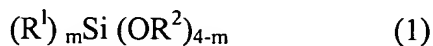
8. (currently amended) The method for forming porous film according to Claim 6 [[or 7]] wherein said step of transforming comprises heating at 150 to 400°C.

9. (currently amended) A porous film obtainable from said composition of ~~any one of Claim~~[[s]] 1 [[to 5]].

10. (currently amended) An interlevel insulator film formable by said composition of ~~any one of Claim~~[[s]] 1 [[to 5]].

11. (currently amended) A semiconductor device comprising internal porous film which is formable by a composition for forming porous film, comprising
a surfactant and

a solution comprising polymer obtainable by hydrolyzing and condensing, in the presence of the surfactant, one or more of alkoxysilane represented by Formula (1) and one or more of alkoxysilane represented by Formula (2):



wherein R^1 represents a monovalent hydrocarbon group which may be substituted or non-substituted and when there are R^1 's, the R^1 's ~~may be~~ are independently the same or different; R^2 represents an alkyl group having 1 to 4 carbons and when there are R^2 's, the R^2 's ~~may be~~ are

independently the same or different; R^3 represents a straight chain or branched alkyl group having 8 to 30 carbons; R^4 represents a monovalent hydrocarbon group which may be substituted or non-substituted and when there are R^4 s, the R^4 s ~~may be~~ are independently the same or different; R^5 represents an alkyl group having 1 to 4 carbons and when there are R^5 s, the R^5 s ~~may be~~ are independently the same or different; m is an integer of 0 to 3; and n is an integer of 0 to 2.

12. (original) The semiconductor device according to Claim 11 wherein said surfactant is a compound which decomposes, evaporates or sublimates when heated to 400°C or less.

13. (currently amended) The semiconductor device according to Claim 11 [[or 12]] wherein said one or more of the alkoxysilanes represented by Formula (2) is [[of]] from 0.01 to 10 parts by weight ~~toward to~~ to 100 parts by weight of said one or more of the alkoxysilanes represented by Formula (1).

14. (currently amended) The semiconductor device according to ~~any one of~~ Claim[[s]] 11 [[to 13]] wherein said one or more of the alkoxysilanes represented by Formula (1) ~~are tetraalkoxysilane and the other compound or compounds; and an amount of the tetraalkoxysilane is 10% by weight or more of tetraalkoxysilane in said alkoxysilanes represented by Formula (1).~~

15. (currently amended) The semiconductor device according to ~~any one of~~ Claim[[s]] 11 [[to 14]], comprising a compound which is neutral at ordinary temperature and generates acid or alkali at 80 to 200°C.

16. (currently amended) The semiconductor device according to ~~any one of~~ Claim[[s]] 11 [[to 15]] wherein said porous film is between metal interconnections in a same layer of multi-level interconnects, or is between upper and lower metal interconnection layers.